

Silicon NPN Power Transistors

2N6496

DESCRIPTION

- With TO-3 package
- High collector current rating
- High power dissipation capability
- Wide area of safe operation

APPLICATIONS

- For switching and amplifier circuits in Industrial and commercial applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

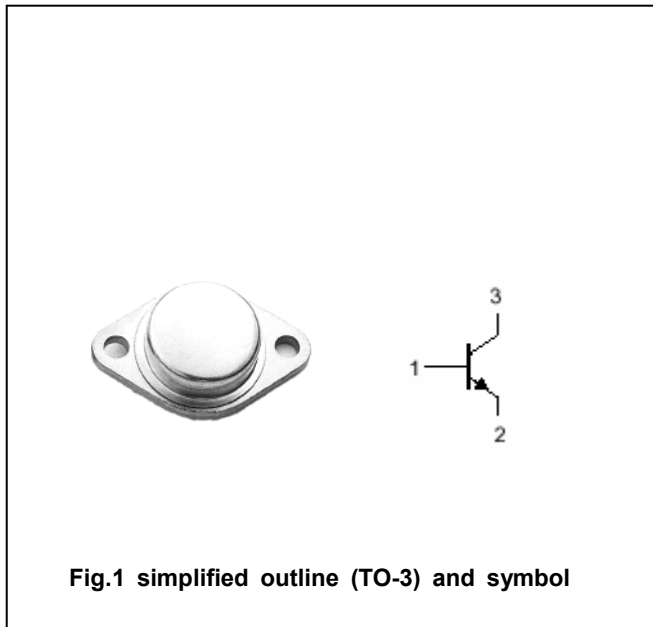


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	110	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _D	Total Power Dissipation	T _C =25□	140	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.25	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =50mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A ; I _B =0.8A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A ; I _B =0.8A			2.0	V
V _{BE}	Base-emitter on voltage	I _C =8A ; V _{CE} =2V			1.8	V
I _{CEO}	Collector cut-off current	V _{CE} =90V; I _B =0			1.0	mA
I _{CEV}	Collector cut-off current	V _{CE} =130V; V _{BE(off)} =1.5V T _C =150°C			2.0 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =8A ; V _{CE} =2V	12		100	
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz			400	pF

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)